

**Amendments to the Claims:**

A listing of the entire set of pending claims is submitted herewith per 37 CFR 1.121. This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Cancel claims 1-11.

12. (Original) A method of constructing a solid state device comprising the steps of:

forming a first layer including an active region and a termination region using a first mask; and

forming at least a second layer including an active region and a termination region using a second mask, the first and second mask being different for the portions corresponding to the termination region.

13. (Original) The method of claim 12 wherein the step of forming at least a second layer includes using a second mask that is substantially identical to the first mask in the portion corresponding to the active region.

14. (Original) A method of forming termination region for a solid state device, the termination region having a width and a depth, the method comprising the steps of:

(a) doping the termination in varying charge concentrations along the width;

and

(b) doping the termination in varying charge concentrations along the depth.

15. (Original) The method of claim 14 wherein the step (a) of doping includes placing discrete deposits of charge of varying volume along a horizontal cross section of said termination region.

16. (Original) The method of claim 14 wherein said steps (a) and (b) comprise doping in concentrations such that field strength along any horizontal or vertical cross section is no greater than 15 volts per micrometer.